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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	416
Number of Logic Elements/Cells	4160
Total RAM Bits	53248
Number of I/O	252
Number of Gates	263000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	356-LBGA
Supplier Device Package	356-BGA (35x35)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/intel/ep20k100bc356-3v">https://www.e-xfl.com/product-detail/intel/ep20k100bc356-3v</a>

Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations

- Altera MegaCore® functions and Altera Megafunction Partners Program (AMPP<sup>SM</sup>) megafunctions
- NativeLink™ integration with popular synthesis, simulation, and timing analysis tools
- Quartus II SignalTap® embedded logic analyzer simplifies in-system design evaluation by giving access to internal nodes during device operation
- Supports popular revision-control software packages including PVCS, Revision Control System (RCS), and Source Code Control System (SCCS )

**Table 4. APEX 20K QFP, BGA & PGA Package Options & I/O Count**    *Notes (1), (2)*

Device	144-Pin TQFP	208-Pin PQFP RQFP	240-Pin PQFP RQFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
EP20K30E	92	125				
EP20K60E	92	148	151	196		
EP20K100	101	159	189	252		
EP20K100E	92	151	183	246		
EP20K160E	88	143	175	271		
EP20K200		144	174	277		
EP20K200E		136	168	271	376	
EP20K300E			152		408	
EP20K400					502	502
EP20K400E					488	
EP20K600E					488	
EP20K1000E					488	
EP20K1500E					488	

**Table 5. APEX 20K FineLine BGA Package Options & I/O Count** *Notes (1), (2)*

Device	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
EP20K30E	93	128			
EP20K60E	93	196			
EP20K100		252			
EP20K100E	93	246			
EP20K160E			316		
EP20K200			382		
EP20K200E			376	376	
EP20K300E				408	
EP20K400				502 (3)	
EP20K400E				488 (3)	
EP20K600E				508 (3)	588
EP20K1000E				508 (3)	708
EP20K1500E					808

**Notes to Tables 4 and 5:**

- (1) I/O counts include dedicated input and clock pins.
- (2) APEX 20K device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), 1.27-mm pitch ball-grid array (BGA), 1.00-mm pitch FineLine BGA, and pin-grid array (PGA) packages.
- (3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

**Table 6. APEX 20K QFP, BGA & PGA Package Sizes**

Feature	144-Pin TQFP	208-Pin QFP	240-Pin QFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
Pitch (mm)	0.50	0.50	0.50	1.27	1.27	—
Area (mm <sup>2</sup> )	484	924	1,218	1,225	2,025	3,906
Length × Width (mm × mm)	22 × 22	30.4 × 30.4	34.9 × 34.9	35 × 35	45 × 45	62.5 × 62.5

**Table 7. APEX 20K FineLine BGA Package Sizes**

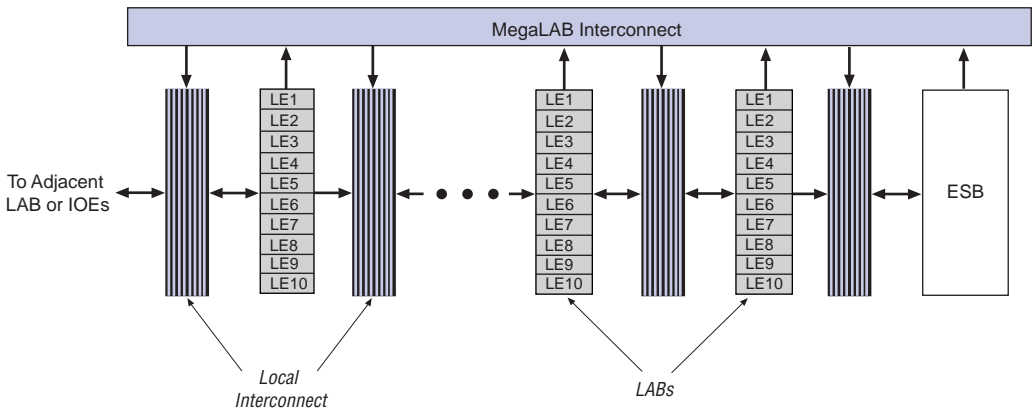
Feature	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm <sup>2</sup> )	169	361	529	729	1,089
Length × Width (mm × mm)	13 × 13	19 × 19	23 × 23	27 × 27	33 × 33

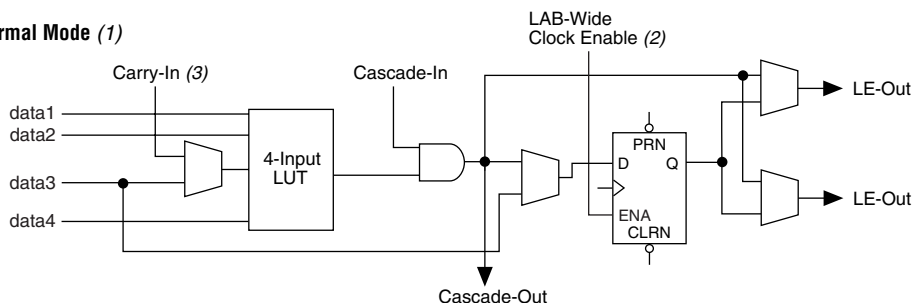
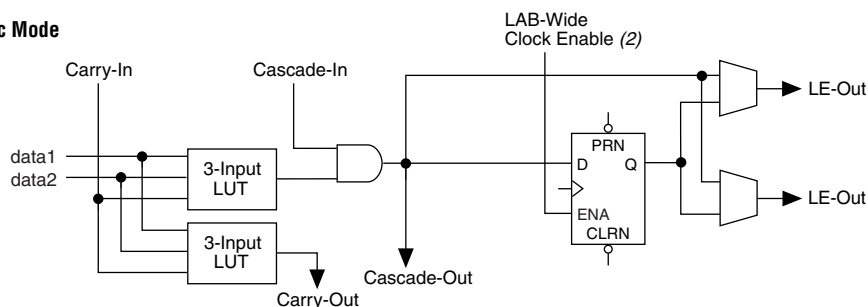
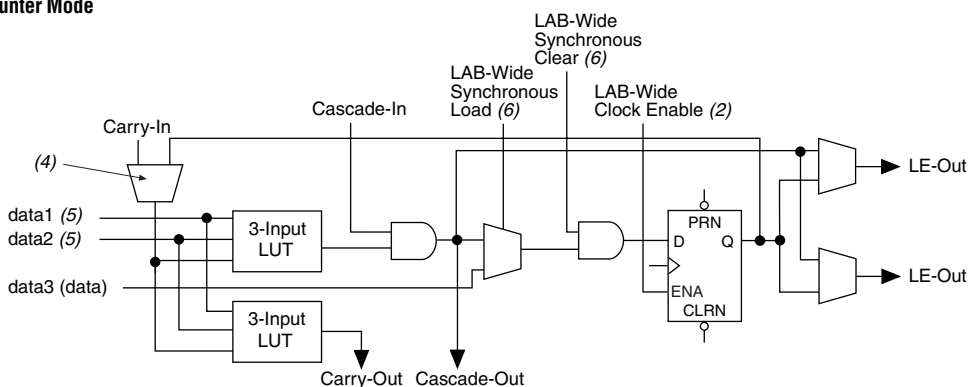
APEX 20K devices provide two dedicated clock pins and four dedicated input pins that drive register control inputs. These signals ensure efficient distribution of high-speed, low-skew control signals. These signals use dedicated routing channels to provide short delays and low skews. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or internally generated asynchronous clear signals with high fan-out. The dedicated clock pins featured on the APEX 20K devices can also feed logic. The devices also feature ClockLock and ClockBoost clock management circuitry. APEX 20KE devices provide two additional dedicated clock pins, for a total of four dedicated clock pins.

MegaLAB Structure

APEX 20K devices are constructed from a series of MegaLAB™ structures. Each MegaLAB structure contains a group of logic array blocks (LABs), one ESB, and a MegaLAB interconnect, which routes signals within the MegaLAB structure. The EP20K30E device has 10 LABs, EP20K60E through EP20K600E devices have 16 LABs, and the EP20K1000E and EP20K1500E devices have 24 LABs. Signals are routed between MegaLAB structures and I/O pins via the FastTrack Interconnect. In addition, edge LABs can be driven by I/O pins through the local interconnect. Figure 2 shows the MegaLAB structure.

Figure 2. MegaLAB Structure



**Figure 8. APEX 20K LE Operating Modes****Normal Mode (1)****Arithmetic Mode****Counter Mode****Notes to Figure 8:**

- (1) LEs in normal mode support register packing.
- (2) There are two LAB-wide clock enables per LAB.
- (3) When using the carry-in in normal mode, the packed register feature is unavailable.
- (4) A register feedback multiplexer is available on LE1 of each LAB.
- (5) The DATA1 and DATA2 input signals can supply counter enable, up or down control, or register feedback signals for LEs other than the second LE in an LAB.
- (6) The LAB-wide synchronous clear and LAB wide synchronous load affect all registers in an LAB.

**Table 9. APEX 20K Routing Scheme**

Source	Destination								
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O Pin					✓	✓	✓	✓	
Column I/O Pin								✓	✓ (1)
LE					✓	✓	✓	✓	
ESB					✓	✓	✓	✓	
Local Interconnect	✓	✓	✓	✓					
MegaLAB Interconnect					✓				
Row FastTrack Interconnect						✓		✓	
Column FastTrack Interconnect						✓	✓		
FastRow Interconnect					✓ (1)				

**Note to Table 9:**

(1) This connection is supported in APEX 20KE devices only.

## Product-Term Logic

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. Each ESB is fed by 32 inputs from the adjacent local interconnect; therefore, it can be driven by the MegaLAB interconnect or the adjacent LAB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

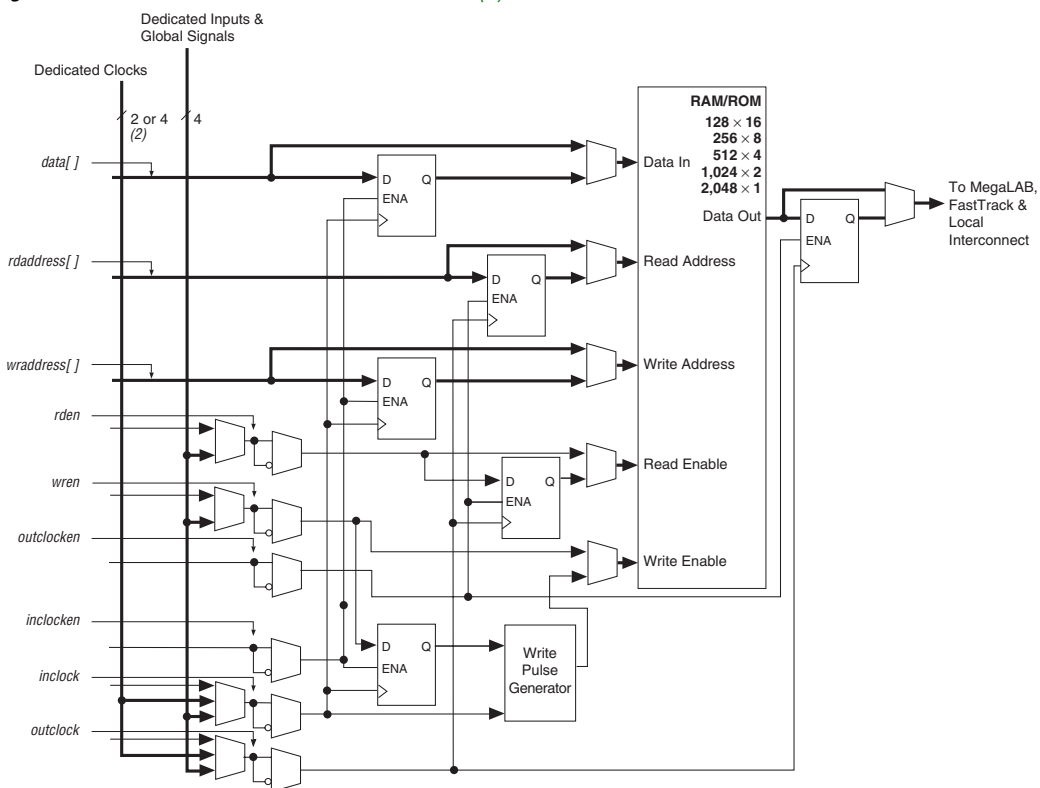
When implementing memory, each ESB can be configured in any of the following sizes:  $128 \times 16$ ,  $256 \times 8$ ,  $512 \times 4$ ,  $1,024 \times 2$ , or  $2,048 \times 1$ . By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two  $128 \times 16$  RAM blocks can be combined to form a  $128 \times 32$  RAM block, and two  $512 \times 4$  RAM blocks can be combined to form a  $512 \times 8$  RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See [Figure 18](#).

## Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

**Figure 20. ESB in Read/Write Clock Mode** *Note (1)*



### Notes to Figure 20:

- (1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
- (2) APEX 20KE devices have four dedicated clocks.



## Advanced I/O Standard Support

APEX 20KE IOEs support the following I/O standards: LVTTTL, LVCMOS, 1.8-V I/O, 2.5-V I/O, 3.3-V PCI, PCI-X, 3.3-V AGP, LVDS, LVPECL, GTL+, CTT, HSTL Class I, SSTL-3 Class I and II, and SSTL-2 Class I and II.



For more information on I/O standards supported by APEX 20KE devices, see *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

The APEX 20KE device contains eight I/O banks. In QFP packages, the banks are linked to form four I/O banks. The I/O banks directly support all standards except LVDS and LVPECL. All I/O banks can support LVDS and LVPECL with the addition of external resistors. In addition, one block within a bank contains circuitry to support high-speed True-LVDS and LVPECL inputs, and another block within a particular bank supports high-speed True-LVDS and LVPECL outputs. The LVDS blocks support all of the I/O standards. Each I/O bank has its own VCCIO pins. A single device can support 1.8-V, 2.5-V, and 3.3-V interfaces; each bank can support a different standard independently. Each bank can also use a separate  $V_{REF}$  level so that each bank can support any of the terminated standards (such as SSTL-3) independently. Within a bank, any one of the terminated standards can be supported. EP20K300E and larger APEX 20KE devices support the LVDS interface for data pins (smaller devices support LVDS clock pins, but not data pins). All EP20K300E and larger devices support the LVDS interface for data pins up to 155 Mbit per channel; EP20K400E devices and larger with an X-suffix on the ordering code add a serializer/deserializer circuit and PLL for higher-speed support.

Each bank can support multiple standards with the same VCCIO for output pins. Each bank can support one voltage-referenced I/O standard, but it can support multiple I/O standards with the same VCCIO voltage level. For example, when VCCIO is 3.3 V, a bank can support LVTTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

When the LVDS banks are not used as LVDS I/O banks, they support all of the other I/O standards. [Figure 29](#) shows the arrangement of the APEX 20KE I/O banks.

**Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2)** Notes (2), (7), (8)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{OL}$	3.3-V low-level TTL output voltage	$I_{OL} = 12 \text{ mA DC}$ , $V_{CCIO} = 3.00 \text{ V}$ (11)			0.45	V
	3.3-V low-level CMOS output voltage	$I_{OL} = 0.1 \text{ mA DC}$ , $V_{CCIO} = 3.00 \text{ V}$ (11)			0.2	V
	3.3-V low-level PCI output voltage	$I_{OL} = 1.5 \text{ mA DC}$ , $V_{CCIO} = 3.00 \text{ to } 3.60 \text{ V}$ (11)			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	$I_{OL} = 0.1 \text{ mA DC}$ , $V_{CCIO} = 2.30 \text{ V}$ (11)			0.2	V
		$I_{OL} = 1 \text{ mA DC}$ , $V_{CCIO} = 2.30 \text{ V}$ (11)			0.4	V
		$I_{OL} = 2 \text{ mA DC}$ , $V_{CCIO} = 2.30 \text{ V}$ (11)			0.7	V
$I_I$	Input pin leakage current	$V_I = 5.75 \text{ to } -0.5 \text{ V}$	-10		10	$\mu\text{A}$
$I_{OZ}$	Tri-stated I/O pin leakage current	$V_O = 5.75 \text{ to } -0.5 \text{ V}$	-10		10	$\mu\text{A}$
$I_{CC0}$	$V_{CC}$ supply current (standby) (All ESBs in power-down mode)	$V_I = \text{ground}$ , no load, no toggling inputs, -1 speed grade (12)		10		mA
		$V_I = \text{ground}$ , no load, no toggling inputs, -2, -3 speed grades (12)		5		mA
$R_{CONF}$	Value of I/O pin pull-up resistor before and during configuration	$V_{CCIO} = 3.0 \text{ V}$ (13)	20		50	W
		$V_{CCIO} = 2.375 \text{ V}$ (13)	30		80	W

**Table 26. APEX 20K 5.0-V Tolerant Device Capacitance** *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
$C_{IN}$	Input capacitance	$V_{IN} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		8	pF
$C_{INCLK}$	Input capacitance on dedicated clock pin	$V_{IN} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		12	pF
$C_{OUT}$	Output capacitance	$V_{OUT} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		8	pF

**Notes to Tables 23 through 26:**

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) All APEX 20K devices are 5.0-V tolerant.
- (3) Minimum DC input is  $-0.5\text{ V}$ . During transitions, the inputs may undershoot to  $-2.0\text{ V}$  or overshoot to  $5.75\text{ V}$  for input currents less than  $100\text{ mA}$  and periods shorter than  $20\text{ ns}$ .
- (4) Numbers in parentheses are for industrial-temperature-range devices.
- (5) Maximum  $V_{CC}$  rise time is  $100\text{ ms}$ , and  $V_{CC}$  must rise monotonically.
- (6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before  $V_{CCINT}$  and  $V_{CCIO}$  are powered.
- (7) Typical values are for  $T_A = 25^\circ\text{C}$ ,  $V_{CCINT} = 2.5\text{ V}$ , and  $V_{CCIO} = 2.5\text{ V}$  or  $3.3\text{ V}$ .
- (8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
- (9) The APEX 20K input buffers are compatible with  $2.5\text{-V}$  and  $3.3\text{-V}$  (LVTTTL and LVC MOS) signals. Additionally, the input buffers are  $3.3\text{-V}$  PCI compliant when  $V_{CCIO}$  and  $V_{CCINT}$  meet the relationship shown in Figure 33 on page 68.
- (10) The  $I_{OH}$  parameter refers to high-level TTL, PCI or CMOS output current.
- (11) The  $I_{OL}$  parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (12) This value is specified for normal device operation. The value may vary during power-up.
- (13) Pin pull-up resistance values will be lower if an external source drives the pin higher than  $V_{CCIO}$ .
- (14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

**Table 27. APEX 20KE Device Absolute Maximum Ratings** *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CCINT}$	Supply voltage	With respect to ground (2)	$-0.5$	2.5	V
$V_{CCIO}$			$-0.5$	4.6	V
$V_I$			$-0.5$	4.6	V
$I_{OUT}$	DC output current, per pin		$-25$	25	mA
$T_{STG}$	Storage temperature	No bias	$-65$	150	$^\circ\text{C}$
$T_{AMB}$	Ambient temperature	Under bias	$-65$	135	$^\circ\text{C}$
$T_J$	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	$^\circ\text{C}$
		Ceramic PGA packages, under bias		150	$^\circ\text{C}$

All specifications are always representative of worst-case supply voltage and junction temperature conditions. All output-pin-timing specifications are reported for maximum driver strength.

Figure 36 shows the  $f_{MAX}$  timing model for APEX 20K devices.

**Figure 36. APEX 20K  $t_{MAX}$  Timing Model**

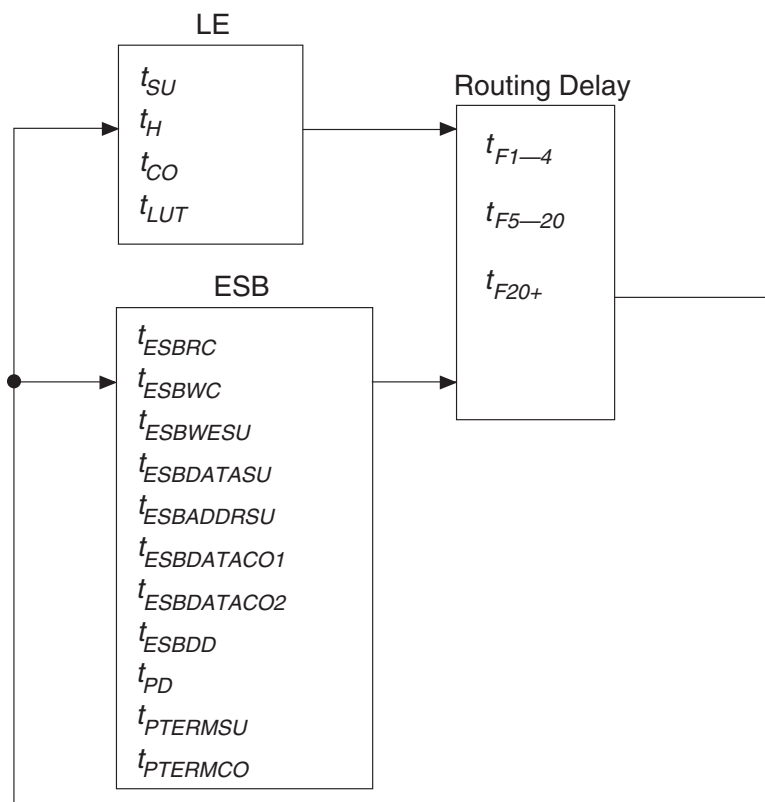


Figure 37 shows the  $f_{MAX}$  timing model for APEX 20KE devices. These parameters can be used to estimate  $f_{MAX}$  for multiple levels of logic. Quartus II software timing analysis should be used for more accurate timing information.

**Table 46. EP20K200 External Bidirectional Timing Parameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}} (1)$	1.9		2.3		2.6		ns
$t_{\text{INHBIDIR}} (1)$	0.0		0.0		0.0		ns
$t_{\text{OUTCOBIDIR}} (1)$	2.0	4.6	2.0	5.6	2.0	6.8	ns
$t_{\text{XZBIDIR}} (1)$		5.0		5.9		6.9	ns
$t_{\text{ZXBIDIR}} (1)$		5.0		5.9		6.9	ns
$t_{\text{INSUBIDIR}} (2)$	1.1		1.2		—		ns
$t_{\text{INHBIDIR}} (2)$	0.0		0.0		—		ns
$t_{\text{OUTCOBIDIR}} (2)$	0.5	2.7	0.5	3.1	—	—	ns
$t_{\text{XZBIDIR}} (2)$		4.3		5.0		—	ns
$t_{\text{ZXBIDIR}} (2)$		4.3		5.0		—	ns

**Table 47. EP20K400 External Timing Parameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSU}} (1)$	1.4		1.8		2.0		ns
$t_{\text{INH}} (1)$	0.0		0.0		0.0		ns
$t_{\text{OUTCO}} (1)$	2.0	4.9	2.0	6.1	2.0	7.0	ns
$t_{\text{INSU}} (2)$	0.4		1.0		—		ns
$t_{\text{INH}} (2)$	0.0		0.0		—		ns
$t_{\text{OUTCO}} (2)$	0.5	3.1	0.5	4.1	—	—	ns

**Table 48. EP20K400 External Bidirectional Timing Parameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}} (1)$	1.4		1.8		2.0		ns
$t_{\text{INHBIDIR}} (1)$	0.0		0.0		0.0		ns
$t_{\text{OUTCOBIDIR}} (1)$	2.0	4.9	2.0	6.1	2.0	7.0	ns
$t_{\text{XZBIDIR}} (1)$		7.3		8.9		10.3	ns
$t_{\text{ZXBIDIR}} (1)$		7.3		8.9		10.3	ns
$t_{\text{INSUBIDIR}} (2)$	0.5		1.0		—		ns
$t_{\text{INHBIDIR}} (2)$	0.0		0.0		—		ns
$t_{\text{OUTCOBIDIR}} (2)$	0.5	3.1	0.5	4.1	—	—	ns
$t_{\text{XZBIDIR}} (2)$		6.2		7.6		—	ns
$t_{\text{ZXBIDIR}} (2)$		6.2		7.6		—	ns

Tables 55 through 60 describe  $f_{MAX}$  LE Timing Microparameters,  $f_{MAX}$  ESB Timing Microparameters,  $f_{MAX}$  Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K60E APEX 20KE devices.

**Table 55. EP20K60E  $f_{MAX}$  LE Timing Microparameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{SU}$	0.17		0.15		0.16		ns
$t_H$	0.32		0.33		0.39		ns
$t_{CO}$		0.29		0.40		0.60	ns
$t_{LUT}$		0.77		1.07		1.59	ns

**Table 69. EP20K160E  $t_{MAX}$  Routing Delays**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{F1-4}$		0.25		0.26		0.28	ns
$t_{F5-20}$		1.00		1.18		1.35	ns
$t_{F20+}$		1.95		2.19		2.30	ns

**Table 70. EP20K160E Minimum Pulse Width Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{CH}$	1.34		1.43		1.55		ns
$t_{CL}$	1.34		1.43		1.55		ns
$t_{CLRP}$	0.18		0.19		0.21		ns
$t_{PREP}$	0.18		0.19		0.21		ns
$t_{ESBCH}$	1.34		1.43		1.55		ns
$t_{ESBCL}$	1.34		1.43		1.55		ns
$t_{ESBWP}$	1.15		1.45		1.73		ns
$t_{ESBRP}$	0.93		1.15		1.38		ns

**Table 71. EP20K160E External Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSU}$	2.23		2.34		2.47		ns
$t_{INH}$	0.00		0.00		0.00		ns
$t_{OUTCO}$	2.00	5.07	2.00	5.59	2.00	6.13	ns
$t_{INSUPLL}$	2.12		2.07		-		ns
$t_{INHPLL}$	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.00	0.50	3.35	-	-	ns

**Table 76. EP20K200E Minimum Pulse Width Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>CH</sub>	1.36		2.44		2.65		ns
t <sub>CL</sub>	1.36		2.44		2.65		ns
t <sub>CLRP</sub>	0.18		0.19		0.21		ns
t <sub>PREP</sub>	0.18		0.19		0.21		ns
t <sub>ESBCH</sub>	1.36		2.44		2.65		ns
t <sub>ESBCL</sub>	1.36		2.44		2.65		ns
t <sub>ESBWP</sub>	1.18		1.48		1.76		ns
t <sub>ESBRP</sub>	0.95		1.17		1.41		ns

**Table 77. EP20K200E External Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>INSU</sub>	2.24		2.35		2.47		ns
t <sub>INH</sub>	0.00		0.00		0.00		ns
t <sub>OUTCO</sub>	2.00	5.12	2.00	5.62	2.00	6.11	ns
t <sub>INSUPLL</sub>	2.13		2.07		-		ns
t <sub>INHPLL</sub>	0.00		0.00		-		ns
t <sub>OUTCOPLL</sub>	0.50	3.01	0.50	3.36	-	-	ns



**Table 78. EP20K200E External Bidirectional Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	2.81		3.19		3.54		ns
$t_{\text{INHBIDIR}}$	0.00		0.00		0.00		ns
$t_{\text{OUTCOBIDIR}}$	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{\text{XZBIDIR}}$		7.51		8.32		8.67	ns
$t_{\text{ZXBIDIR}}$		7.51		8.32		8.67	ns
$t_{\text{INSUBIDIRPLL}}$	3.30		3.64		-		ns
$t_{\text{INHBIDIRPLL}}$	0.00		0.00		-		ns
$t_{\text{OUTCOBIDIRPLL}}$	0.50	3.01	0.50	3.36	-	-	ns
$t_{\text{XZBIDIRPLL}}$		5.40		6.05		-	ns
$t_{\text{ZXBIDIRPLL}}$		5.40		6.05		-	ns

Tables 79 through 84 describe  $f_{\text{MAX}}$  LE Timing Microparameters,  $f_{\text{MAX}}$  ESB Timing Microparameters,  $f_{\text{MAX}}$  Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K300E APEX 20KE devices.

**Table 79. EP20K300E  $f_{\text{MAX}}$  LE Timing Microparameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{SU}}$	0.16		0.17		0.18		ns
$t_{\text{H}}$	0.31		0.33		0.38		ns
$t_{\text{CO}}$		0.28		0.38		0.51	ns
$t_{\text{LUT}}$		0.79		1.07		1.43	ns

Tables 97 through 102 describe  $f_{MAX}$  LE Timing Microparameters,  $f_{MAX}$  ESB Timing Microparameters,  $f_{MAX}$  Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1000E APEX 20KE devices.

**Table 97. EP20K1000E  $f_{MAX}$  LE Timing Microparameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{SU}$	0.25		0.25		0.25		ns
$t_H$	0.25		0.25		0.25		ns
$t_{CO}$		0.28		0.32		0.33	ns
$t_{LUT}$		0.80		0.95		1.13	ns

**Table 104. EP20K1500E  $f_{MAX}$  ESB Timing Microparameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{ESBARC}$		1.78		2.02		1.95	ns
$t_{ESBSRC}$		2.52		2.91		3.14	ns
$t_{ESBAWC}$		3.52		4.11		4.40	ns
$t_{ESBSWC}$		3.23		3.84		4.16	ns
$t_{ESBWASU}$	0.62		0.67		0.61		ns
$t_{ESBWAH}$	0.41		0.55		0.55		ns
$t_{ESBWDSU}$	0.77		0.79		0.81		ns
$t_{ESBWDH}$	0.41		0.55		0.55		ns
$t_{ESBRASU}$	1.74		1.92		1.85		ns
$t_{ESBRAH}$	0.00		0.01		0.23		ns
$t_{ESBWESU}$	2.07		2.28		2.41		ns
$t_{ESBWEH}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.25		0.27		0.29		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.04		0.11		ns
$t_{ESBRADDRSU}$	0.14		0.11		0.16		ns
$t_{ESBDATAO1}$		1.29		1.50		1.63	ns
$t_{ESBDATAO2}$		2.55		2.99		3.22	ns
$t_{ESBDD}$		3.12		3.57		3.85	ns
$t_{PD}$		1.84		2.13		2.32	ns
$t_{PTERMSU}$	1.08		1.19		1.32		ns
$t_{PTERMCO}$		1.31		1.53		1.66	ns

**Table 105. EP20K1500E  $f_{MAX}$  Routing Delays**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{F1-4}$		0.28		0.28		0.28	ns
$t_{F5-20}$		1.36		1.50		1.62	ns
$t_{F20+}$		4.43		4.48		5.07	ns

**Table 110. Selectable I/O Standard Output Delays**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVC MOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.09		0.10	ns
1.8 V		2.49		2.98		3.03	ns
PCI		−0.03		0.17		0.16	ns
GTL+		0.75		0.75		0.76	ns
SSTL-3 Class I		1.39		1.51		1.50	ns
SSTL-3 Class II		1.11		1.23		1.23	ns
SSTL-2 Class I		1.35		1.48		1.47	ns
SSTL-2 Class II		1.00		1.12		1.12	ns
LVDS		−0.48		−0.48		−0.48	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

## Power Consumption

To estimate device power consumption, use the interactive power calculator on the Altera web site at <http://www.altera.com>.

## Configuration & Operation

The APEX 20K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

### Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to  $V_{CCIO}$  by a built-in weak pull-up resistor.

## Version 4.1

*APEX 20K Programmable Logic Device Family Data Sheet* version 4.1 contains the following changes:

- $t_{ESBWEH}$  added to [Figure 37](#) and [Tables 35, 50, 56, 62, 68, 74, 86, 92, 97, and 104](#).
- Updated EP20K300E device internal and external timing numbers in [Tables 79 through 84](#).